

# HAT2080T

Silicon N Channel MOS FET  
High Speed Power Switching

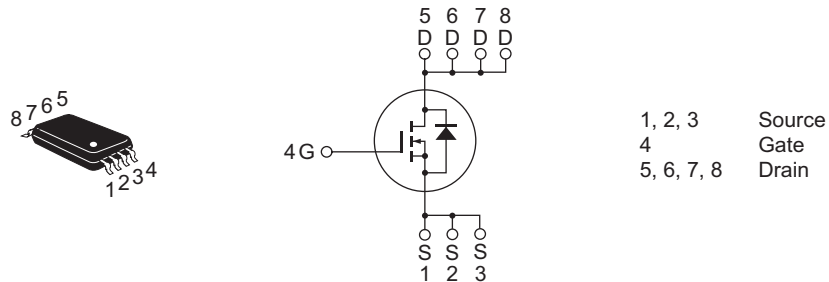
REJ03G0162-0500  
(Previous: ADE-208-1026C)  
Rev.5.00  
Sep 07, 2005

## Features

- Low on-resistance
- Low drive current
- High density mounting

## Outline

RENESAS Package code: PTSP0008JB-A  
(Package name: TSSOP-8 <TTP-8D> )



## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	250	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	1.2	A
Drain peak current	I <sub>D (pulse)</sub> <sup>Note 1</sup>	9.6	A
Body to drain diode reverse drain current	I <sub>DR</sub>	1.2	A
Channel dissipation	P <sub>ch</sub> <sup>Note 2</sup>	1.3	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

www.DataSheet4U.com 2. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s

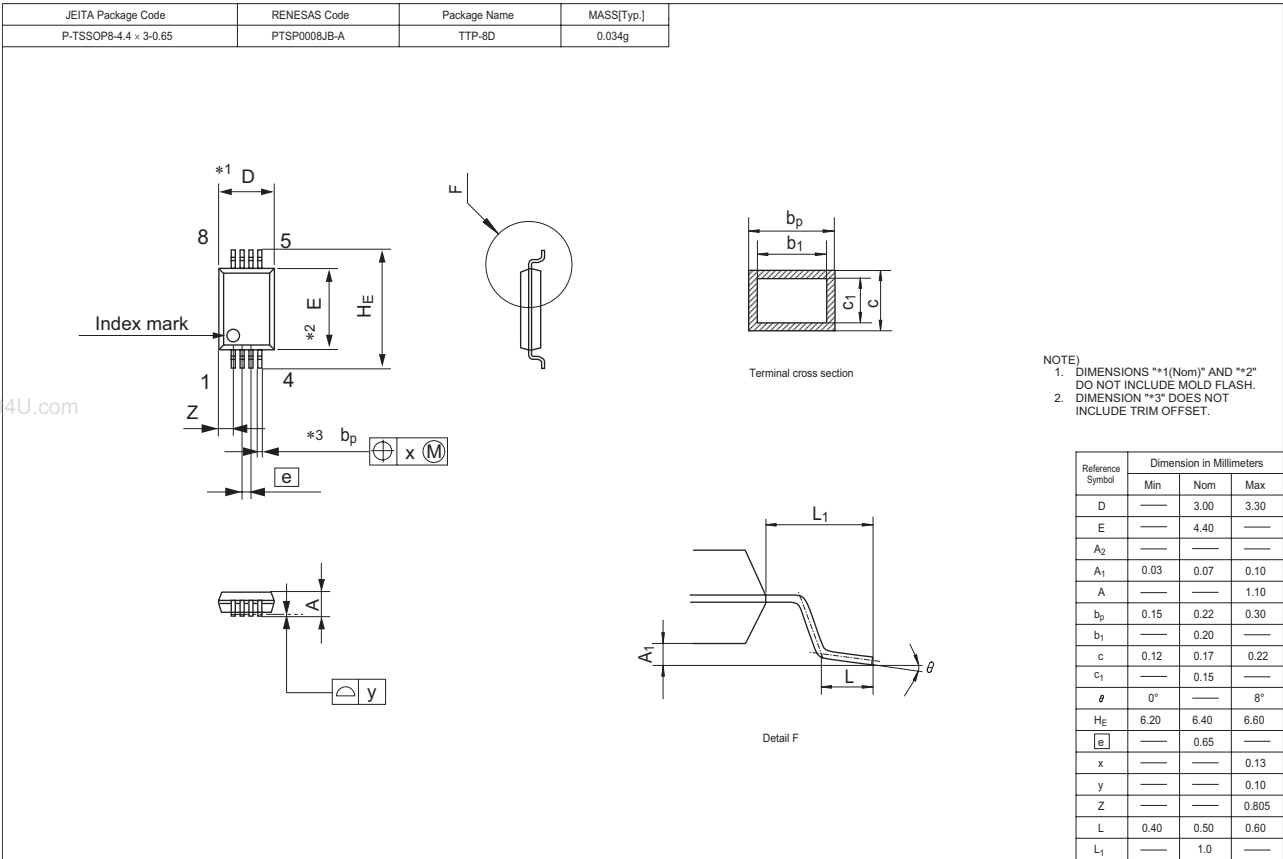
## Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR) DSS</sub>	250	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±0.1	μA	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS (off)</sub>	3.0	—	4.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS (on)</sub>	—	0.65	0.85	Ω	I <sub>D</sub> = 0.6 A, V <sub>GS</sub> = 10 V <sup>Note 3</sup>
Forward transfer admittance	y <sub>fs</sub>	0.9	1.5	—	S	I <sub>D</sub> = 0.6 A, V <sub>DS</sub> = 10 V <sup>Note 3</sup>
Input capacitance	C <sub>iss</sub>	—	300	—	pF	V <sub>DS</sub> = 25 V
Output capacitance	C <sub>oss</sub>	—	42	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	C <sub>rss</sub>	—	11	—	pF	f = 1 MHz
Turn-on delay time	t <sub>d (on)</sub>	—	18	—	ns	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 0.6 A
Rise time	t <sub>r</sub>	—	10	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d (off)</sub>	—	48	—	ns	R <sub>L</sub> = 208 Ω
Fall time	t <sub>f</sub>	—	23	—	ns	R <sub>g</sub> = 10 Ω
Total gate charge	Q <sub>g</sub>	—	11	—	nC	V <sub>DD</sub> = 200 V
Gate to source charge	Q <sub>gs</sub>	—	1.5	—	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Q <sub>gd</sub>	—	5	—	nC	I <sub>D</sub> = 1.2 A
Body to drain diode forward voltage	V <sub>DF</sub>	—	0.8	1.2	V	I <sub>F</sub> = 1.2 A, V <sub>GS</sub> = 0 <sup>Note 3</sup>
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	70	—	ns	I <sub>F</sub> = 1.2 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 100 A/μs

Note: 3. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2080T-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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